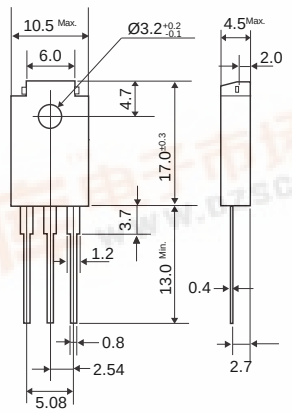
ESAC33M(C,N,D) (8A) (200V / 8A)

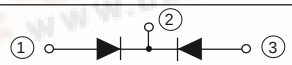
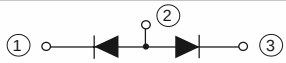
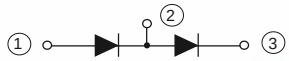
FAST RECOVERY DIODE

Outline drawings, mm



JEDEC	———
EIAJ	SC-67

Connection diagram

ESAC33M-□□C	
ESAC33M-□□N	
ESAC33M-□□D	

Features

- Insulated package by fully molding
- High voltage by mesa design
- High reliability

Applications

- High speed switching

Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating -02	Unit
Repetitive peak reverse voltage	V_{RRM}		200	V
Non-repetitive peak reverse voltage	V_{RSM}		200	V
Average output current	Io	Square wave, duty=1/2, Tc=95°C	8*	A
Surge current	I_{FSM}	Sine wave 10ms	30	A
Operating junction temperature	T_j		-40 to +150	°C
Storage temperature	T_{stg}		-40 to +150	°C

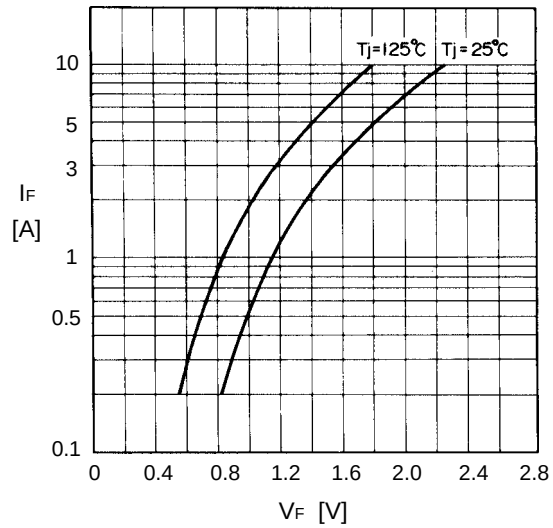
*Average forward current of centertap full wave connection

- Electrical characteristics (Ta=25°C Unless otherwise specified)

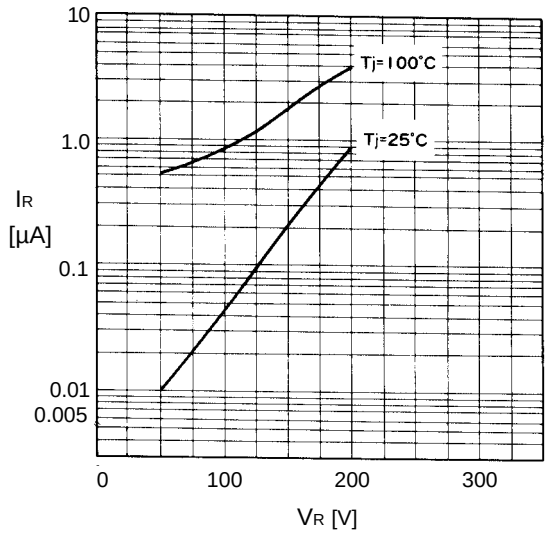
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	I_{FM}=2.0A	1.4	V
Reverse current	I_{RRM}	V_R=V_{RRM}	500	μA
Reverse recovery time	t rr	I_F=0.1A, I_R=0.1A	100	ns
Thermal resistance	$R_{th(j-c)}$	Junction to case	3.5	°C/W

■ Characteristics

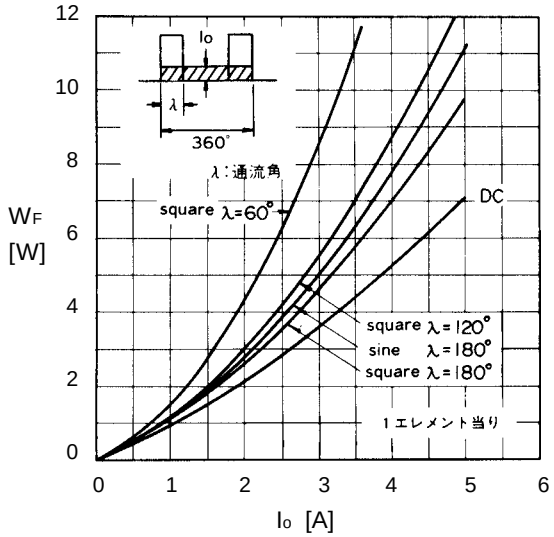
Forward characteristics



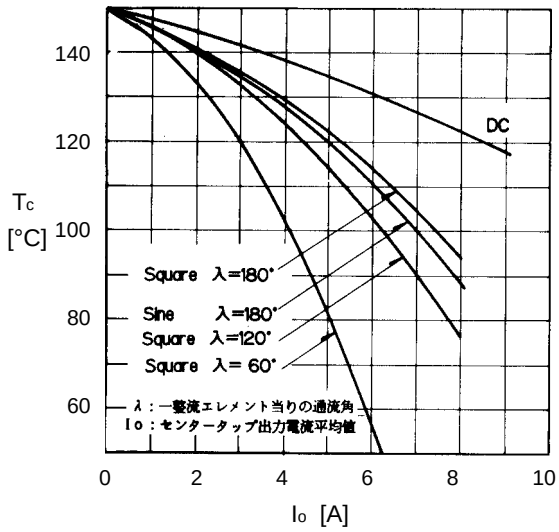
Reverse characteristics



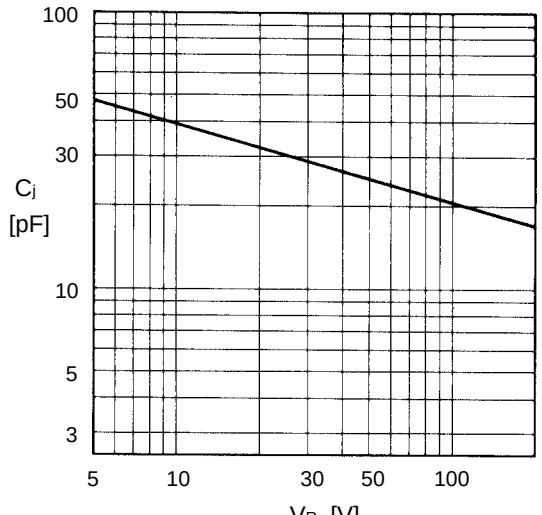
Forward power dissipation



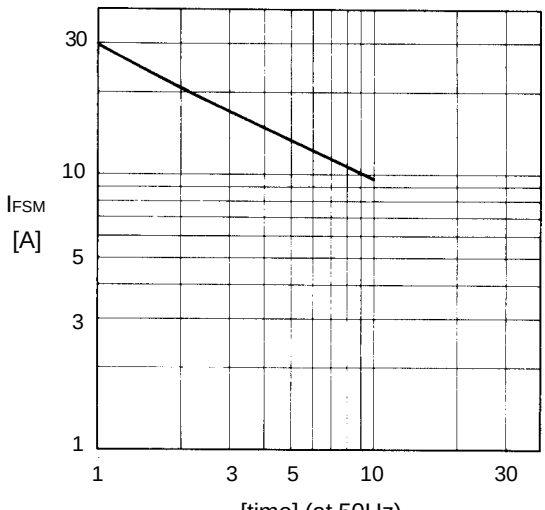
Output current-case temperature



Junction capacitance characteristics



Surge capability



Transient thermal impedance